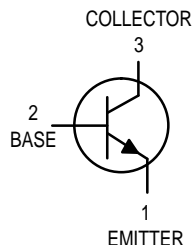


General Purpose Transistors

NPN Silicon

2N4400
2N4401*

*Motorola Preferred Device



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}, I_E = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 0.1 \text{ mAdc}, I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 0.1 \text{ mAdc}, I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 35 \text{ Vdc}, V_{EB} = 0.4 \text{ Vdc}$)	I_{BEV}	—	0.1	μAdc
Collector Cutoff Current ($V_{CE} = 35 \text{ Vdc}, V_{EB} = 0.4 \text{ Vdc}$)	I_{CEX}	—	0.1	μAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS(1)				
DC Current Gain ($I_C = 0.1 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N4401	20	—	—
($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N4400 2N4401	20 40	— —	—
($I_C = 10 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N4400 2N4401	40 80	— —	—
($I_C = 150 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	2N4400 2N4401	50 100	150 300	—
($I_C = 500 \text{ mAdc}$, $V_{CE} = 2.0 \text{ Vdc}$)	2N4400 2N4401	20 40	— —	—
Collector–Emitter Saturation Voltage ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	$V_{CE(sat)}$	— —	0.4 0.75	Vdc
Base–Emitter Saturation Voltage ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	$V_{BE(sat)}$	0.75 —	0.95 1.2	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 20 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 100 \text{ MHz}$)	2N4400 2N4401	f_T	200 250	— —	MHz
Collector–Base Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)		C_{cb}	—	6.5	pF
Emitter–Base Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)		C_{eb}	—	30	pF
Input Impedance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	2N4400 2N4401	h_{ie}	0.5 1.0	7.5 15	k ohms
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)		h_{re}	0.1	8.0	$\times 10^{-4}$
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	2N4400 2N4401	h_{fe}	20 40	250 500	—
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)		h_{oe}	1.0	30	μmhos

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 30 \text{ Vdc}$, $V_{BE} = 2.0 \text{ Vdc}$, $I_C = 150 \text{ mAdc}$, $I_{B1} = 15 \text{ mAdc}$)	t_d	—	15	ns
Rise Time		t_r	—	20	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}$, $I_C = 150 \text{ mAdc}$, $I_{B1} = I_{B2} = 15 \text{ mAdc}$)	t_s	—	225	ns
Fall Time		t_f	—	30	ns

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

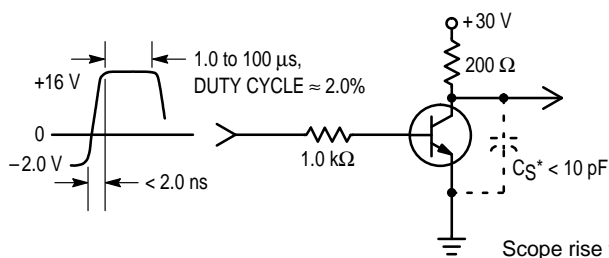


Figure 1. Turn–On Time

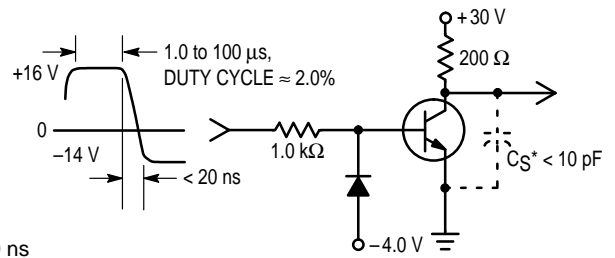


Figure 2. Turn–Off Time

TRANSIENT CHARACTERISTICS

— 25°C - - - 100°C

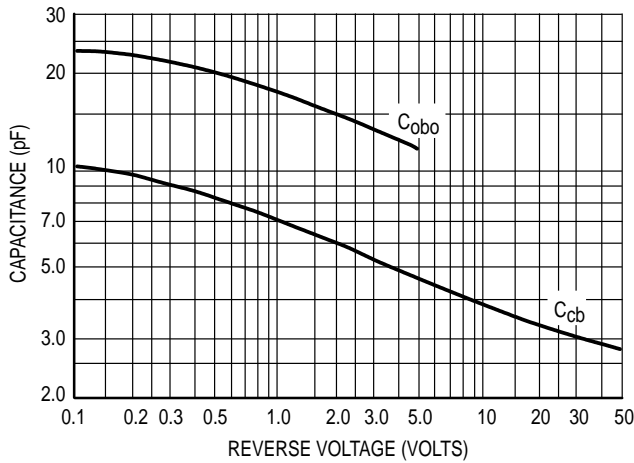


Figure 3. Capacitances

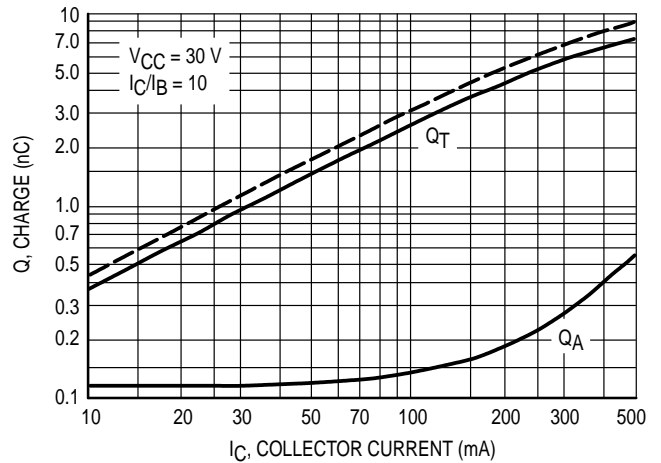


Figure 4. Charge Data

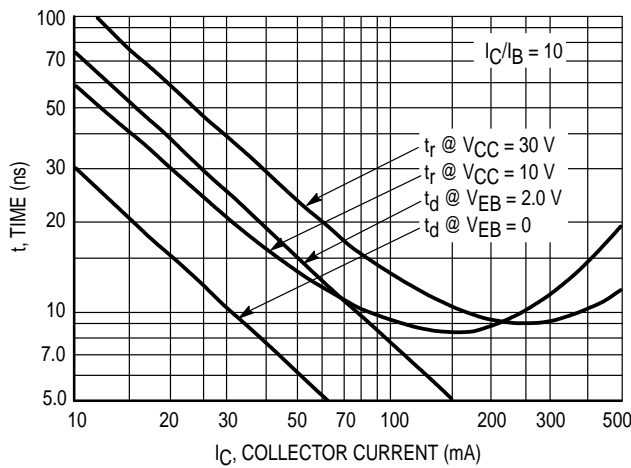


Figure 5. Turn-On Time

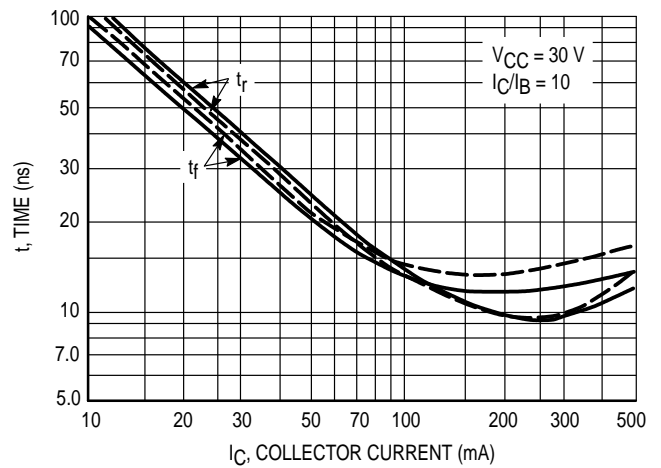


Figure 6. Rise and Fall Times

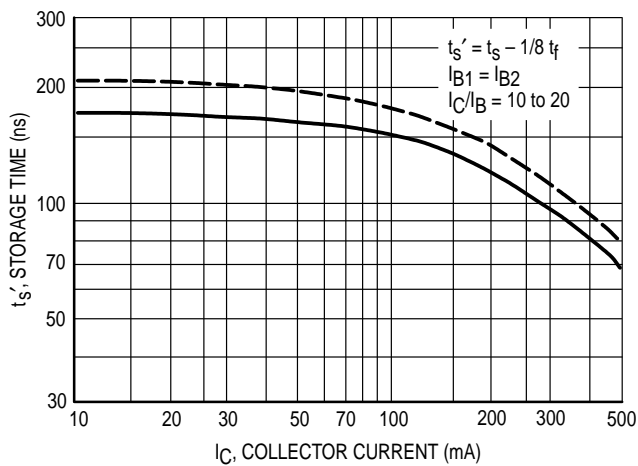


Figure 7. Storage Time

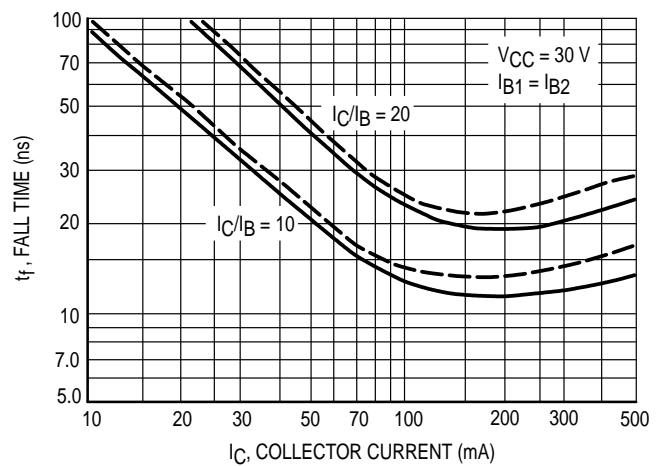


Figure 8. Fall Time

SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$
Bandwidth = 1.0 Hz

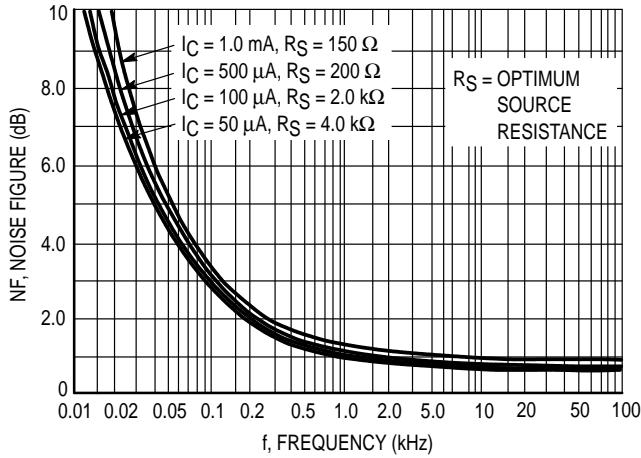


Figure 9. Frequency Effects

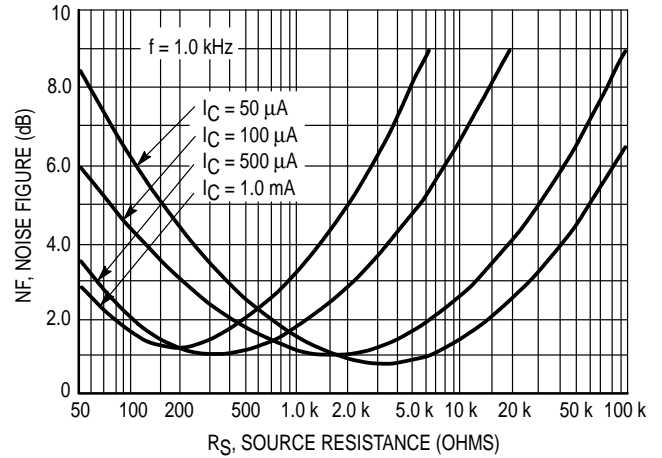


Figure 10. Source Resistance Effects

h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were

selected from both the 2N4400 and 2N4401 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

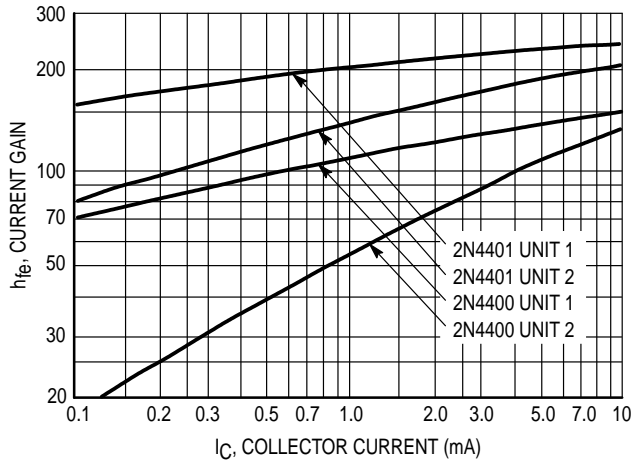


Figure 11. Current Gain

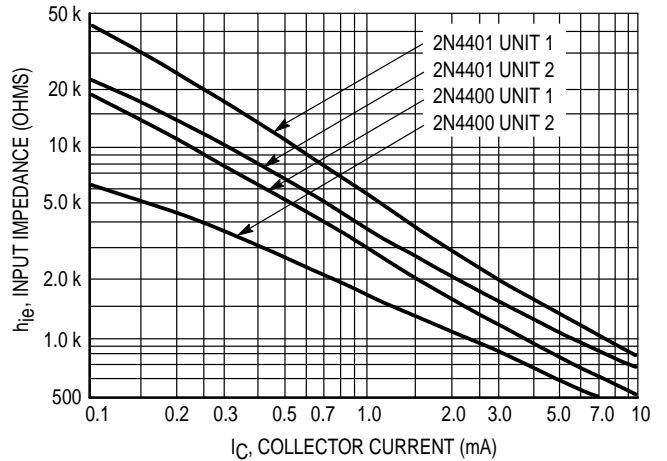


Figure 12. Input Impedance

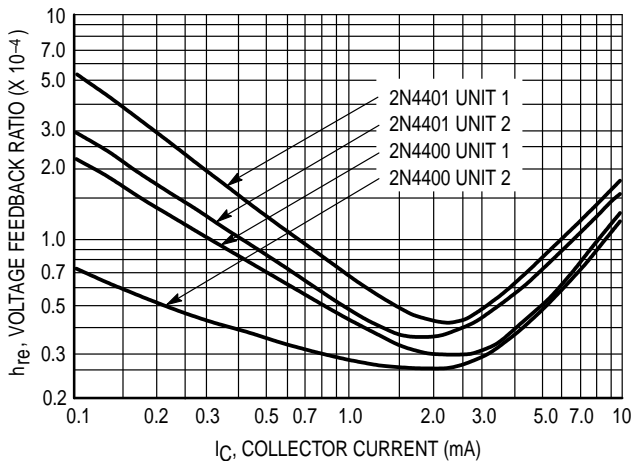


Figure 13. Voltage Feedback Ratio

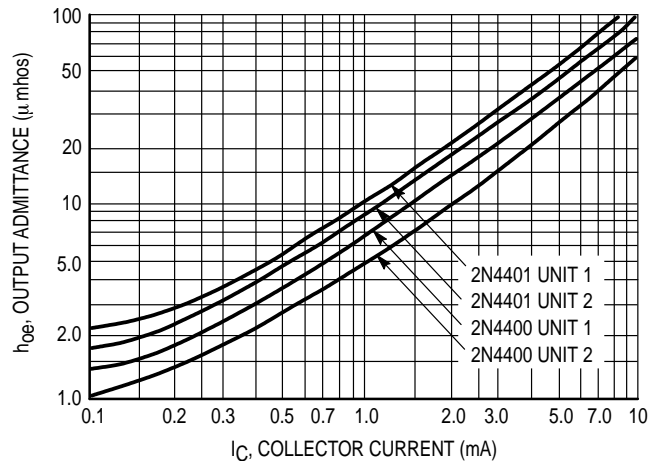


Figure 14. Output Admittance

STATIC CHARACTERISTICS

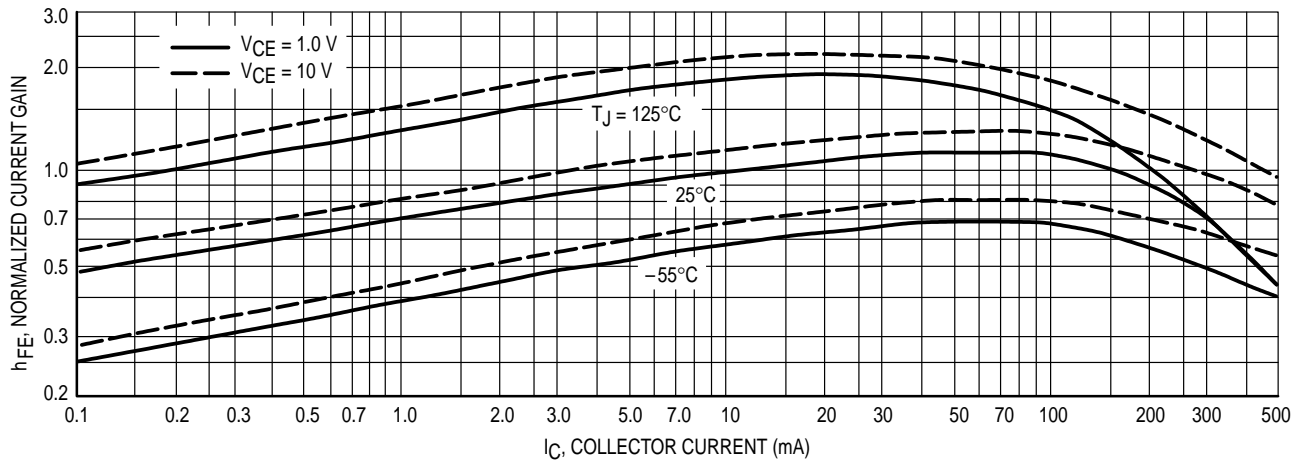


Figure 15. DC Current Gain

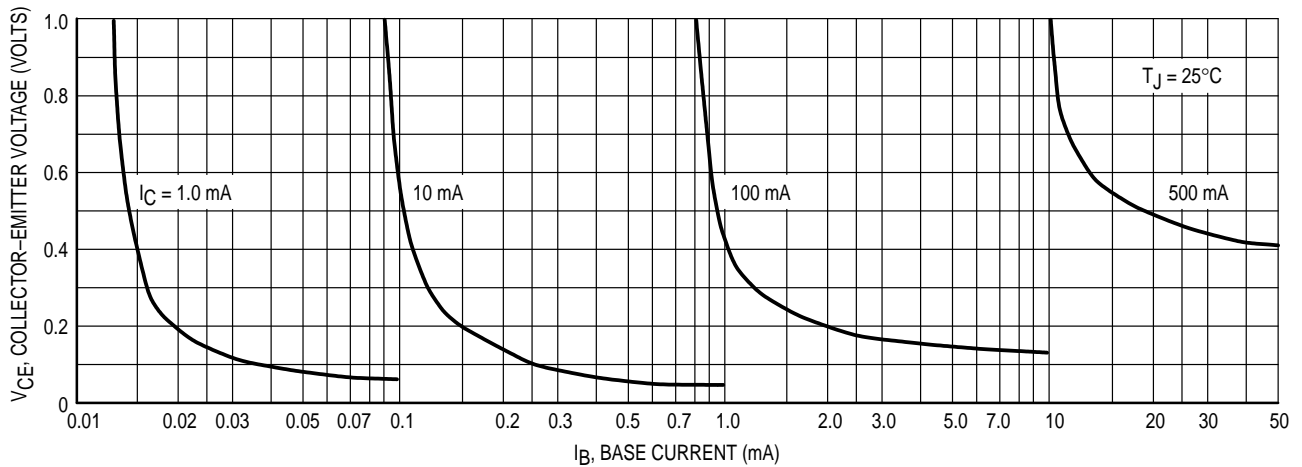


Figure 16. Collector Saturation Region

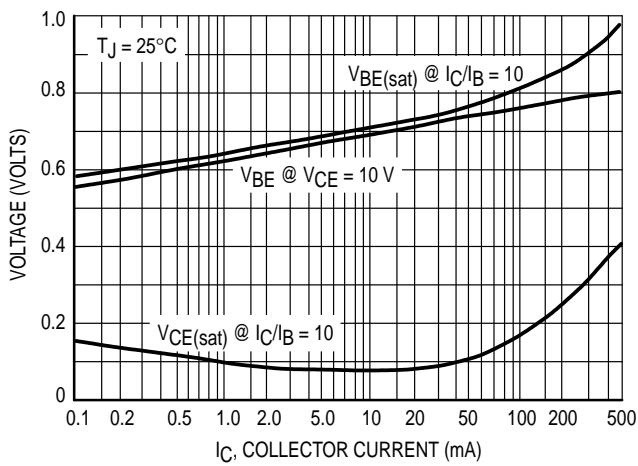


Figure 17. "On" Voltages

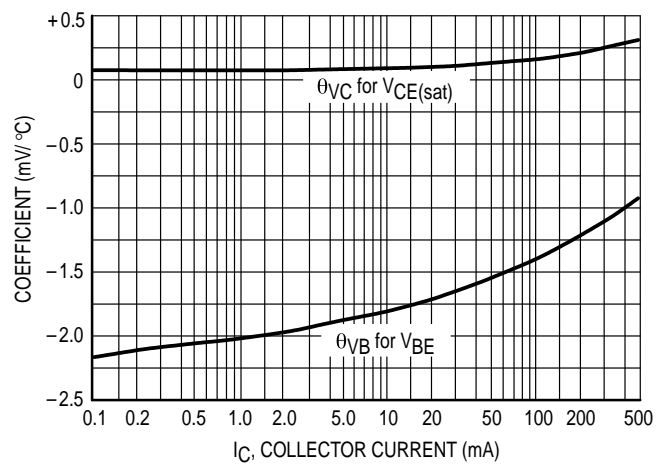
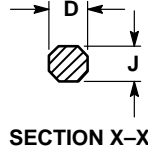
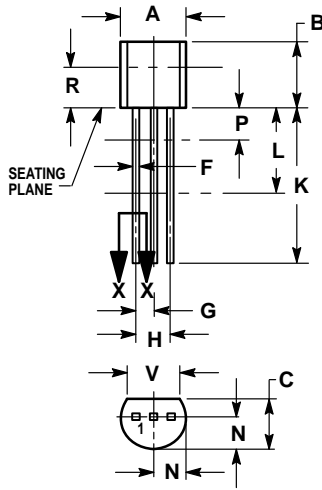


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS



CASE 029-04
(TO-226AA)
ISSUE AD

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K. MINIMUM LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

- STYLE 1:
1. EMITTER
 2. BASE
 3. COLLECTOR

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:
USA/EUROPE: Motorola Literature Distribution;
P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki,
6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609
INTERNET: http://Design-NET.com

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

